

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
-100V	150mΩ @ V <sub>GS</sub> = -10V	-15A
	190mΩ @ V <sub>GS</sub> = -6V	-14A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor controls

## Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DIODES™ ZXMP10A18KQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

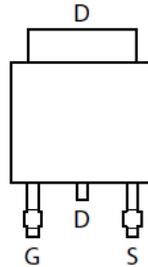
## Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.315 grams (Approximate)

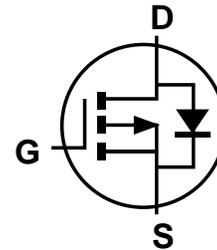
TO252 (DPAK)



Top View



Top View  
Pin Out



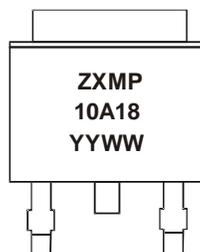
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
ZXMP10A18KQTC	TO252 (DPAK)	2,500	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



ZXMP10A18 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 22 = 2022)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	-15
		T <sub>C</sub> = +70°C	-12
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-32	A
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	-15	A
Pulsed Source Current (10μs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	-32	A
Avalanche Current, L = 1mH	I <sub>AS</sub>	-12.5	A
Avalanche Energy, L = 1mH	E <sub>AS</sub>	78	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	38	°C/W
Total Power Dissipation	P <sub>D</sub>	3.3	W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	1.75	°C/W
Total Power Dissipation	P <sub>D</sub>	71	W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-2	—	-4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	92	150	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.8A
		—	109	190		V <sub>GS</sub> = -6V, I <sub>D</sub> = -2.4A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.8	-0.95	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.5A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	1055	—	pF	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	90	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	76	—	pF	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.9	—	ns	V <sub>DS</sub> = -50V, V <sub>GS</sub> = -10V I <sub>D</sub> = -1A, R <sub>G</sub> = 6Ω
Rise Time	t <sub>R</sub>	—	6.8	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	33.9	—		
Rise Time	t <sub>F</sub>	—	17.9	—		
Total Gate Charge	Q <sub>g</sub>	—	26.9	—	nC	V <sub>DS</sub> = -50V, V <sub>GS</sub> = -10V I <sub>D</sub> = -2.8A
Gate-Source Charge	Q <sub>gs</sub>	—	3.9	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	10.2	—		
Reverse Recovery Time	t <sub>RR</sub>	—	49	—	ns	I <sub>S</sub> = -2.8A, dI/dt = 100A/μs
Reverse Recovery Charge	Q <sub>R</sub>	—	107	—	nC	

- Notes:
5. Thermal resistance from junction to soldering point (on the exposed drain pad).
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

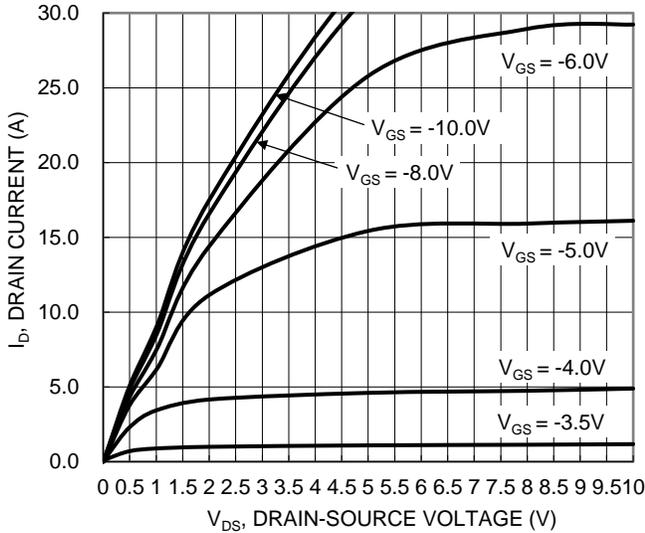


Figure 1. Typical Output Characteristic

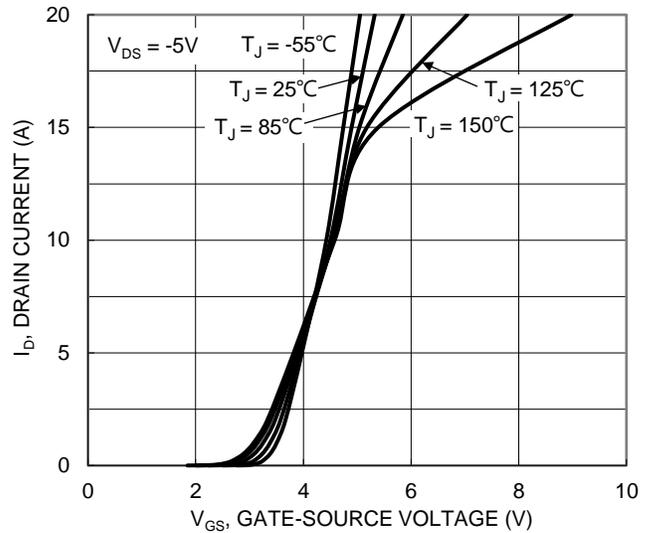


Figure 2. Typical Transfer Characteristic

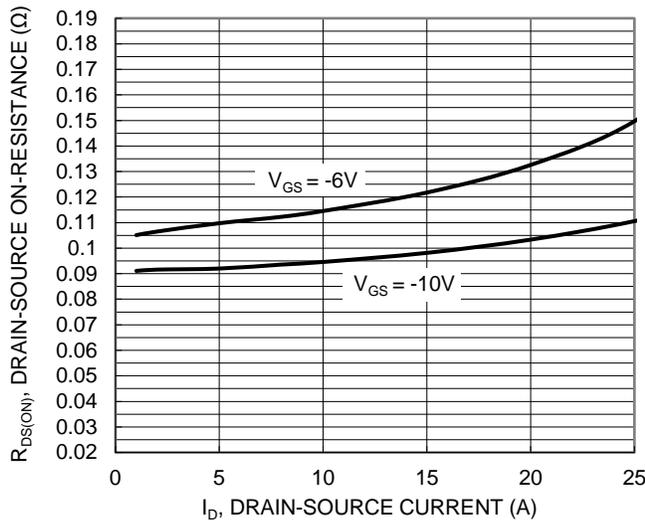


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

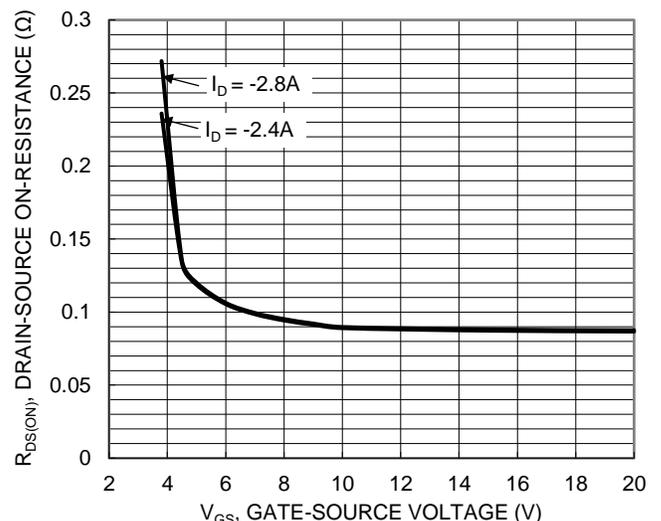


Figure 4. Typical Transfer Characteristic

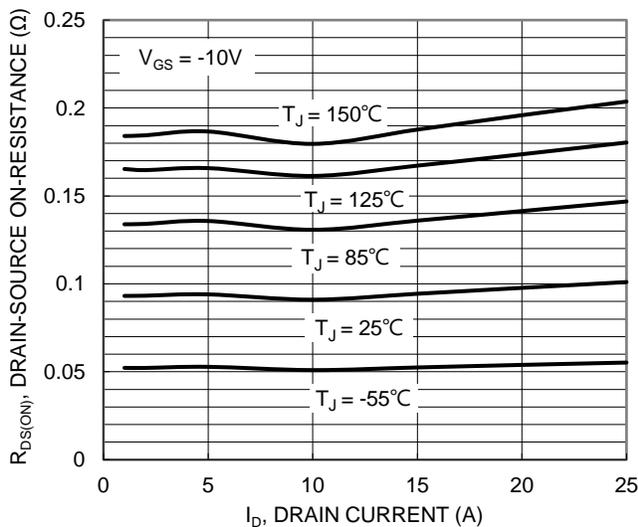


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

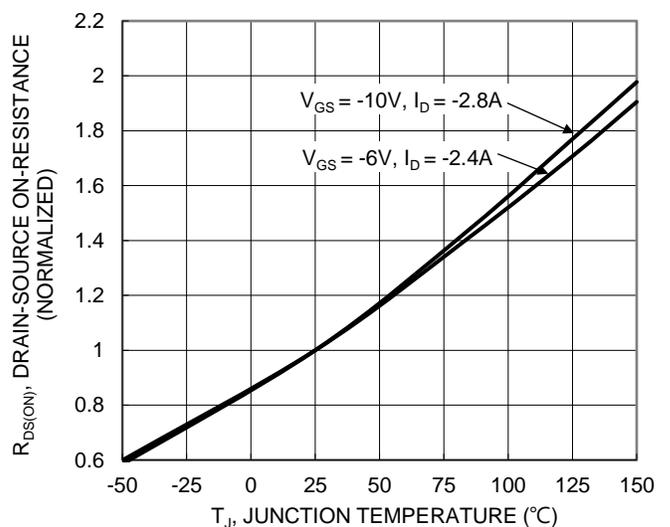


Figure 6. On-Resistance Variation with Junction Temperature

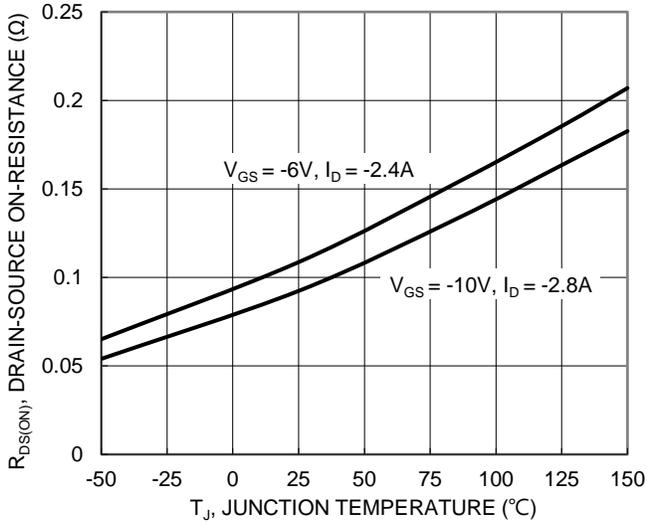


Figure 7. On-Resistance Variation with Junction Temperature

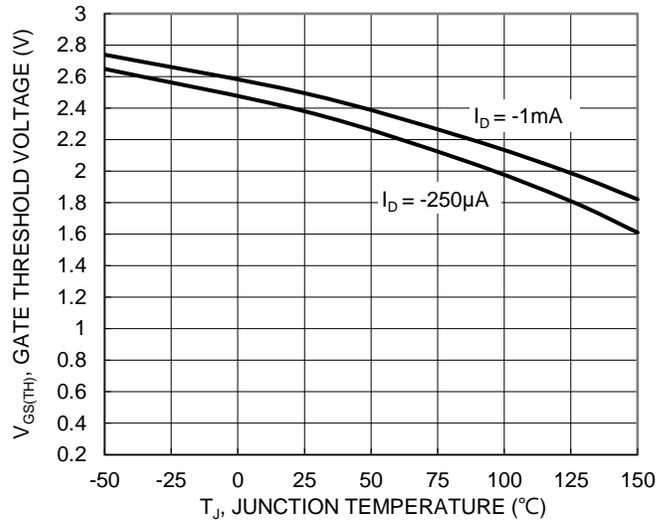


Figure 8. Gate Threshold Variation vs Junction Temperature

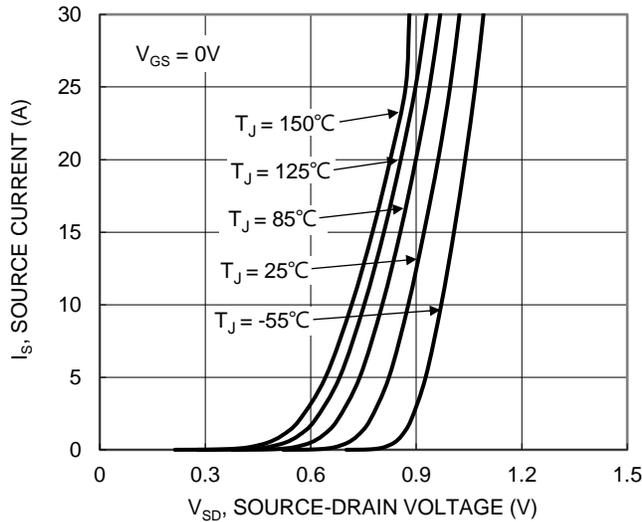


Figure 9. Diode Forward Voltage vs. Current

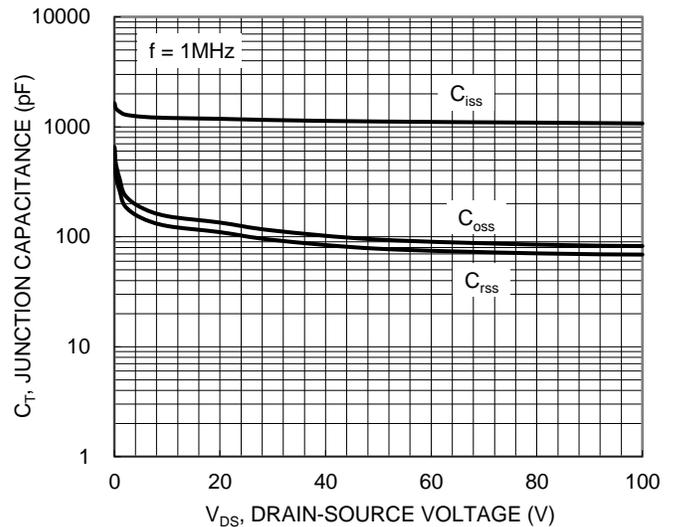


Figure 10. Typical Junction Capacitance

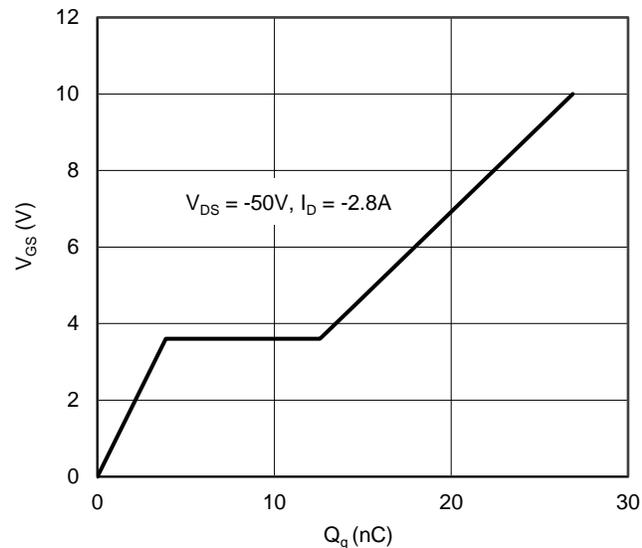


Figure 11. Gate Charge

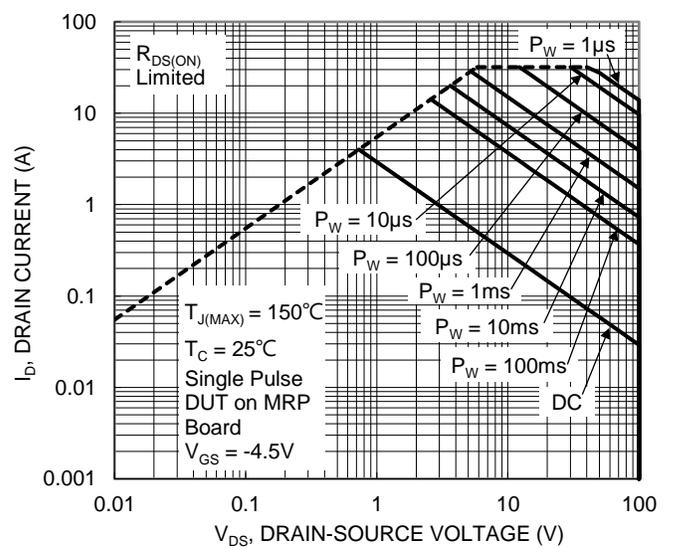


Figure 12. SOA, Safe Operation Area

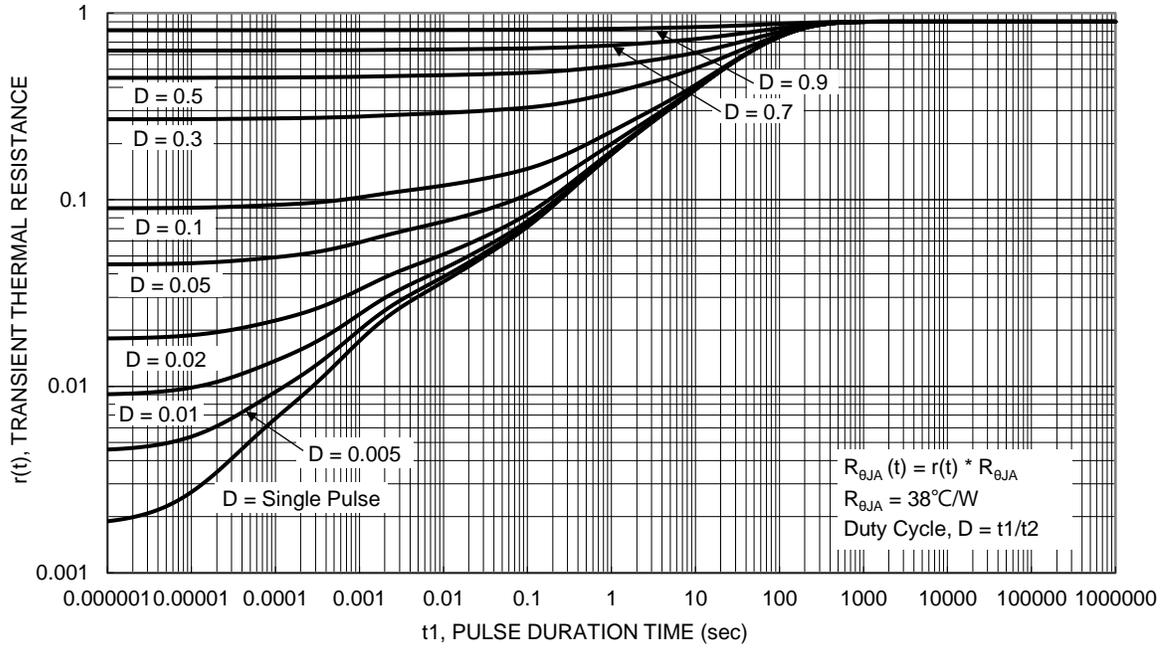
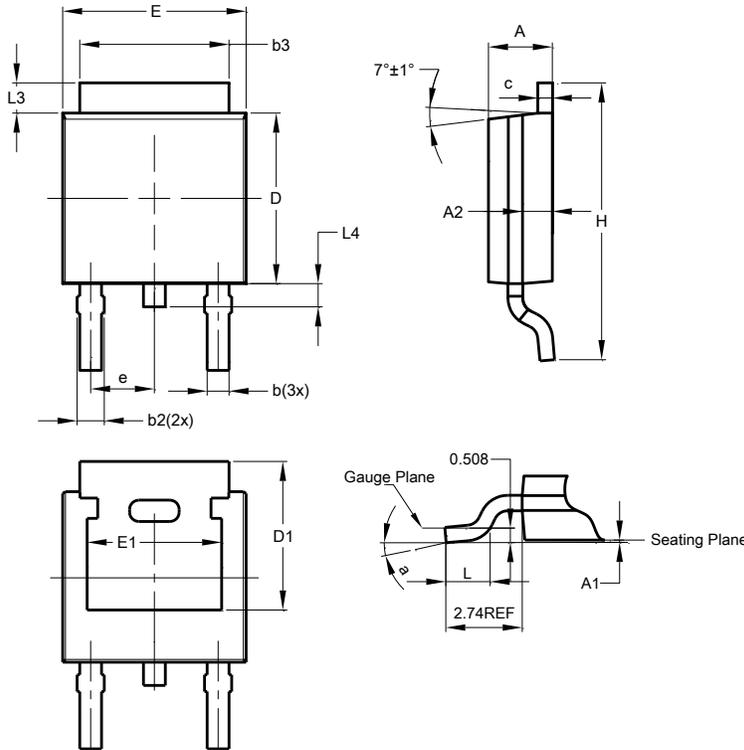


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO252 (DPAK)**

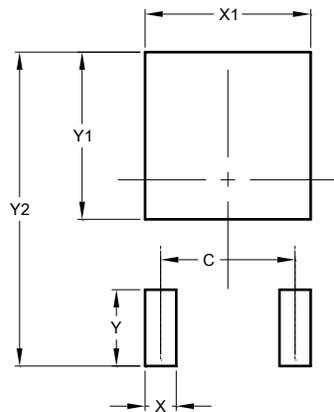


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO252 (DPAK)**



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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